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FIG. 1 A



FIG. 1 B

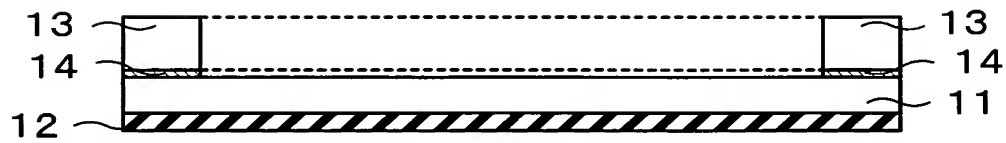


FIG. 1 C

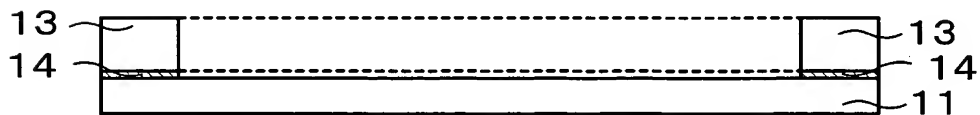


FIG. 1 D

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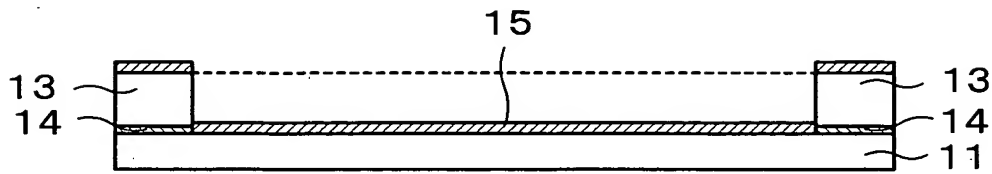


FIG. 1 E

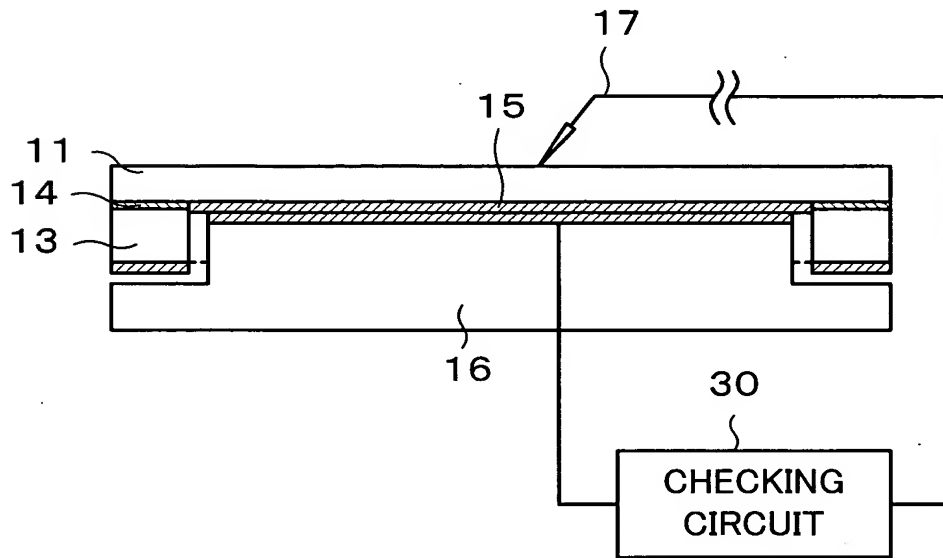


FIG. 1 F

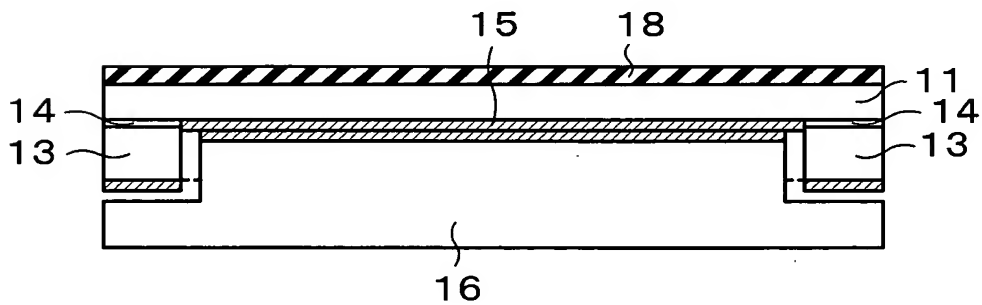


FIG. 1 G

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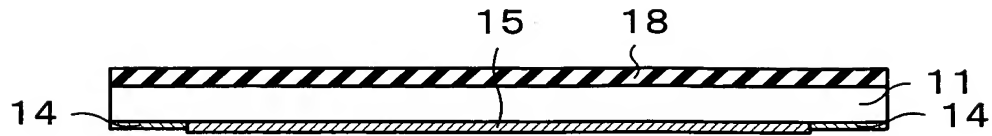


FIG. 1 H

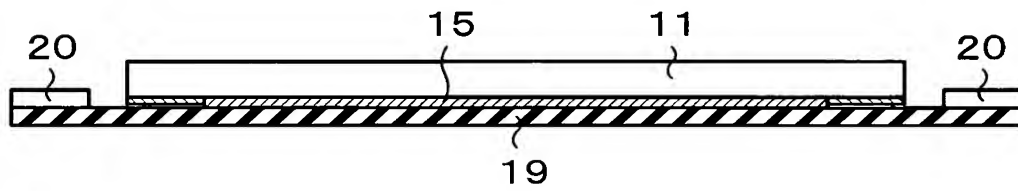


FIG. 1 I

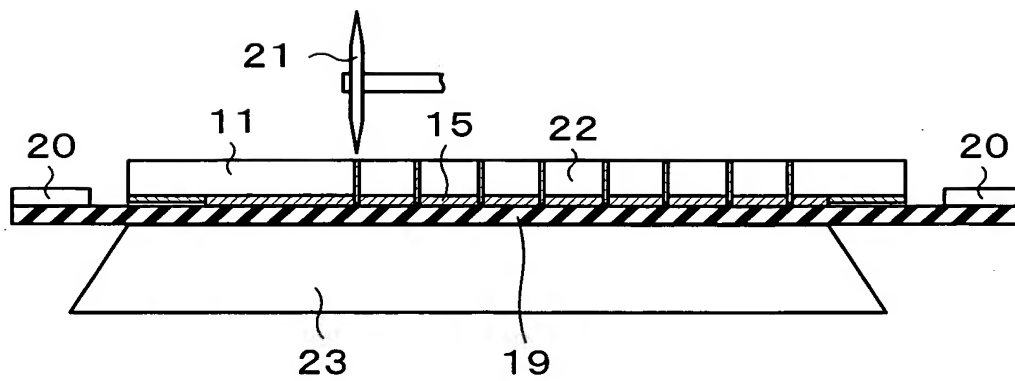


FIG. 1 J

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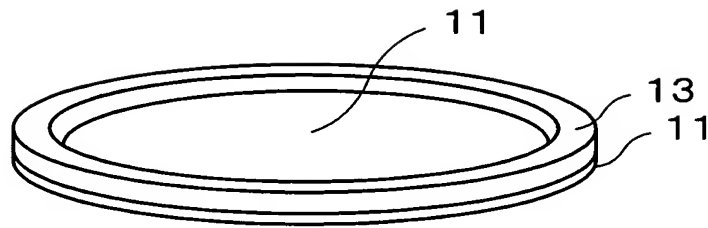


FIG. 2

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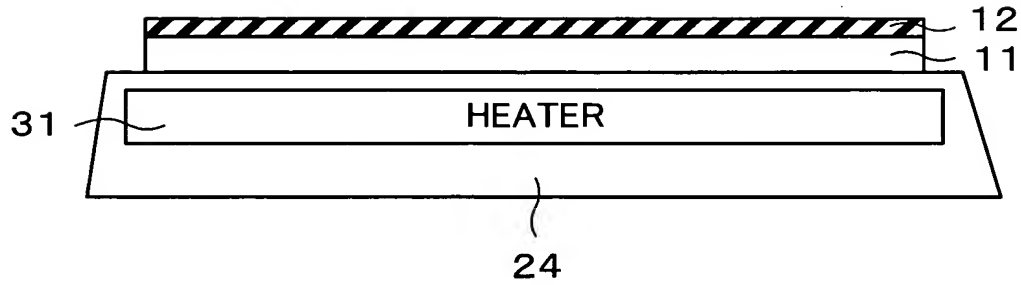


FIG. 3A

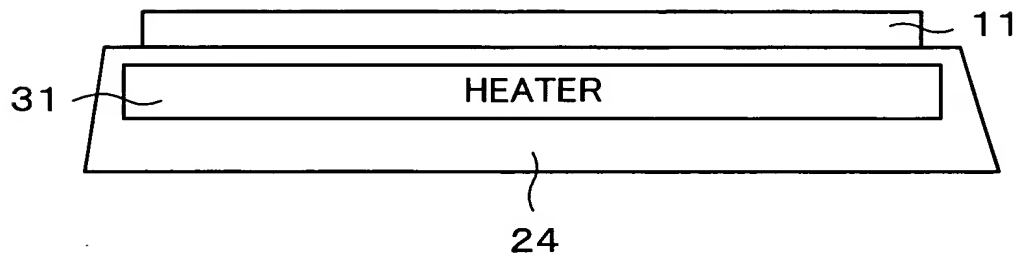


FIG. 3B

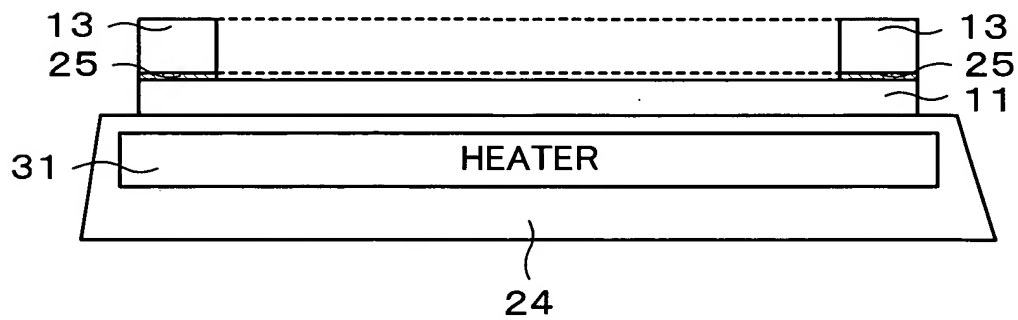


FIG. 3C

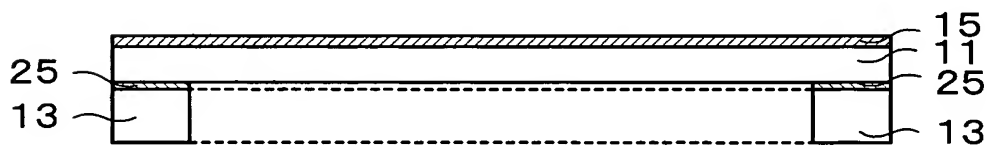


FIG. 3D

A cross-sectional view of a semiconductor device. A thin layer 11 is formed on a substrate 15. The substrate 15 is divided into two main regions, 26 and 30. A contact 13 is formed on the left side of layer 11, and another contact 25 is formed on the right side. A probe 27 is shown touching the surface of layer 11. A checking circuit 30 is connected to the right side of the substrate 15.

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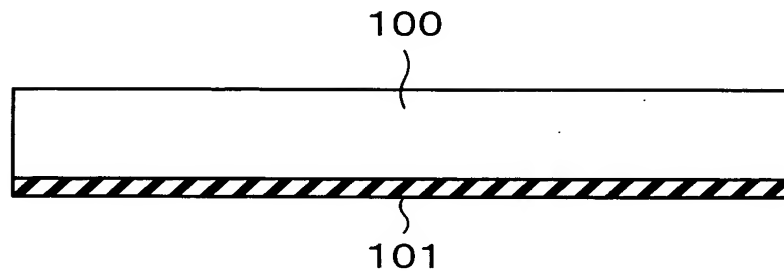


FIG. 4A

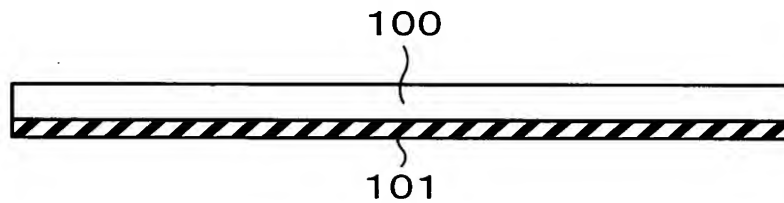


FIG. 4B

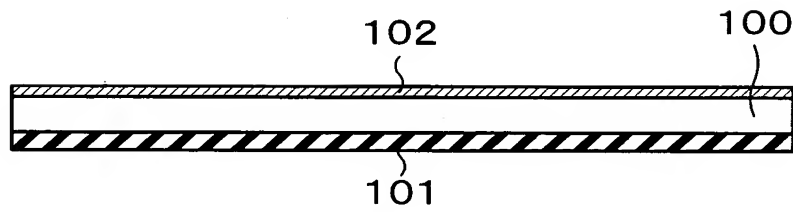


FIG. 4C

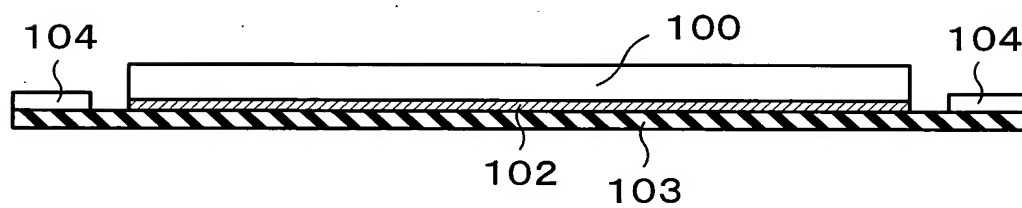


FIG. 4D

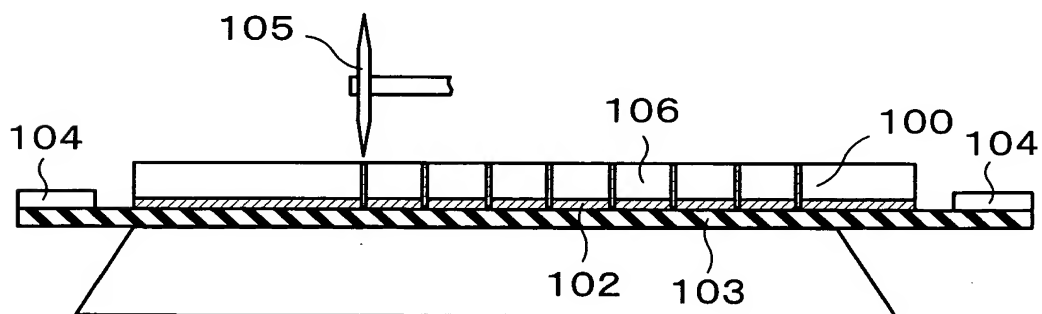


FIG. 4E